2SC4097

Rev.E Mar.-2016

ˇYت / Descriptions

Silicon NPN transistor in a SOT-323 Plastic Package.

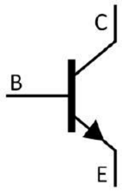
◕ È / Features

Low C_{ob}, complements the 2SA1577.

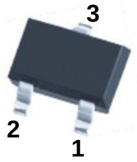
ﾜ ﮢ / Applications

Medium power transistor.

ᥫﯙ ᾇ ؏ ع / Equivalent Circuit



ẫ ﾉ ưँ / Pinning



PIN1 Emitter PIN 2 Base PIN 3 Collector

ե ਸ ᄂ / Marking

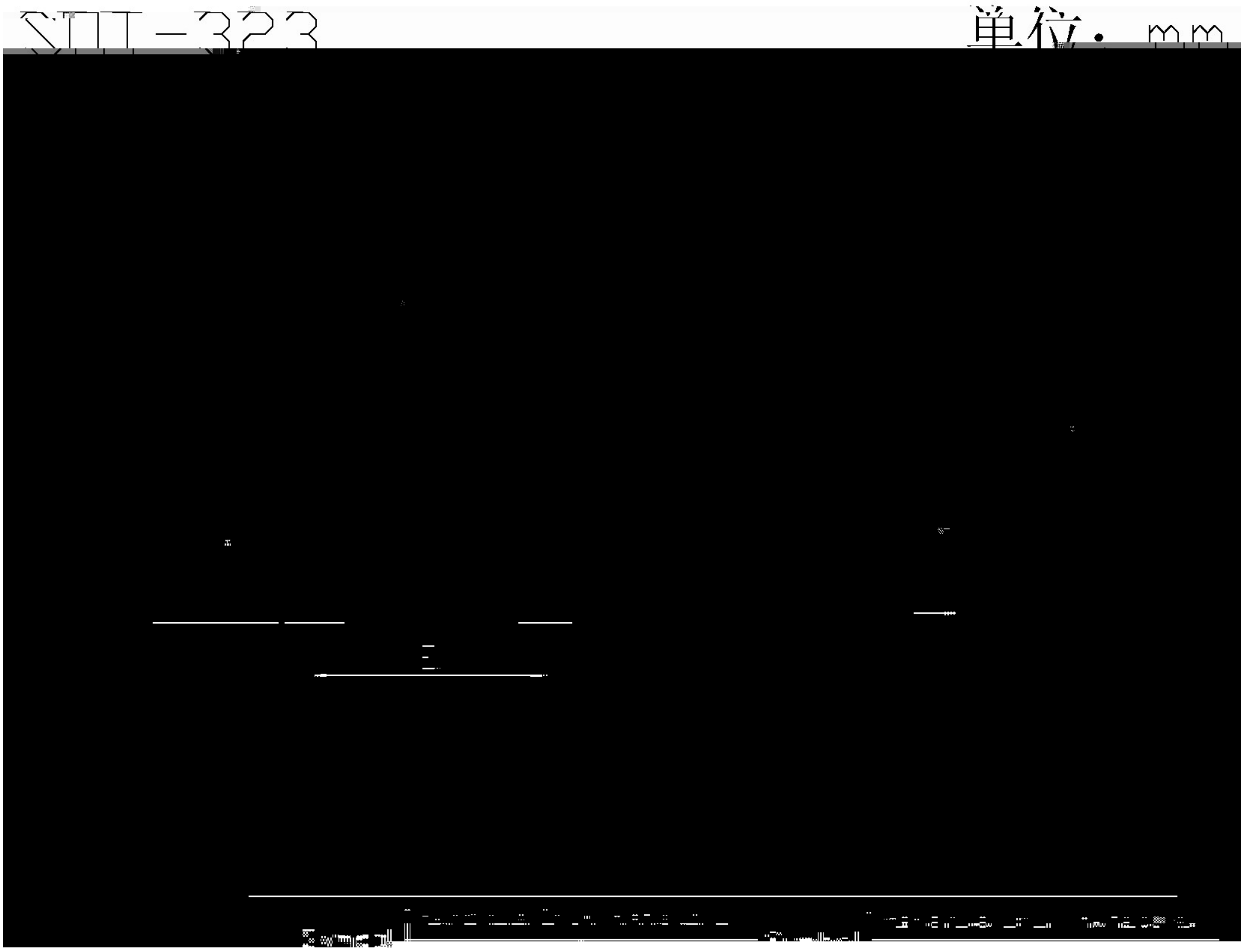
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HCP	HCQ	HCR

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

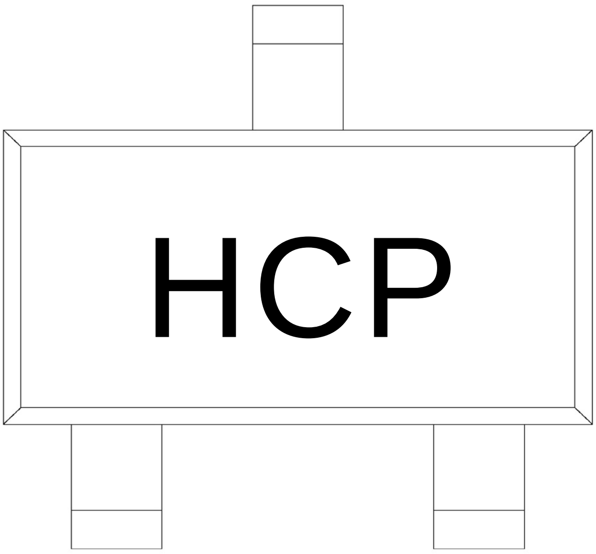
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100 A I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	32			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100 A I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			1.0	A
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			1.0	A
DC Current Gain	h_{FE}	V_{CE}=3.0V I_C I				

≠ Ʒ Ặ΄E ꟿ ʃ / Electrical Characteristic Curve

ᵘ ẺỒ Ḽ ʃ / Package Dimensions



ł˛ L˝Ω / Marking Instructions



H

C

P h_{FE}

Note:

H: Company Code.

C: Product Type.

P: h_{FE} Classifications Symbol

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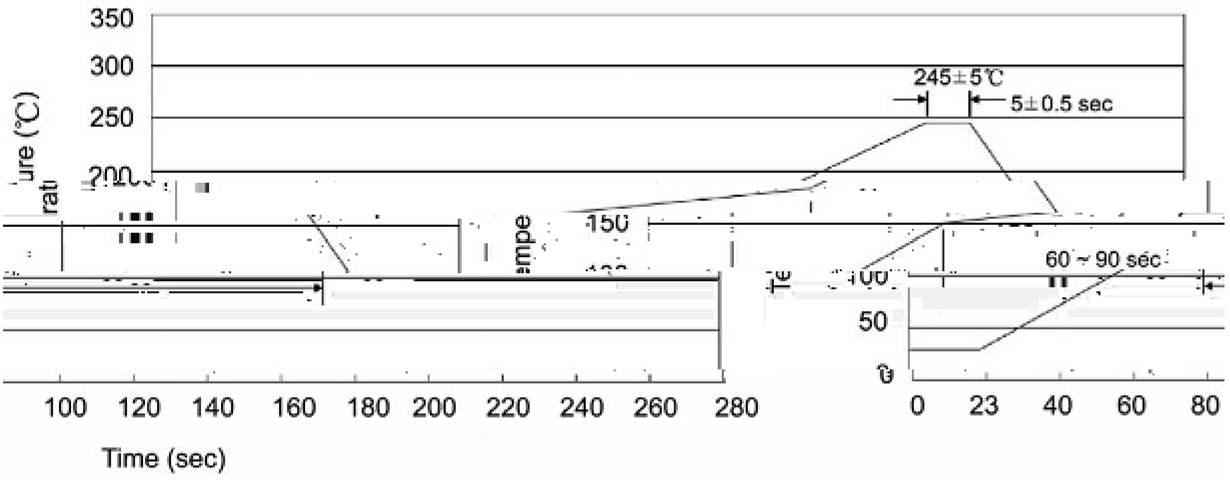

1 25 150 60 90sec;
2 245 5 5 0.5sec;
3 2 10 /sec.

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:245 5 , Duration:5 0.5sec.
3.